



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

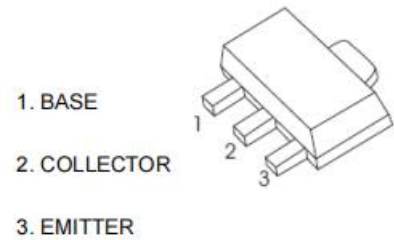
2SB1260

SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

PNP General Purpose 通用

■ Absolute Maximum Ratings 最大额定值



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-80	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-80	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-1000	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

■ Device Marking 产品打标

H_{FE}	82-180(P)	120-270(Q)	180-390(R)
Mark	ZL		

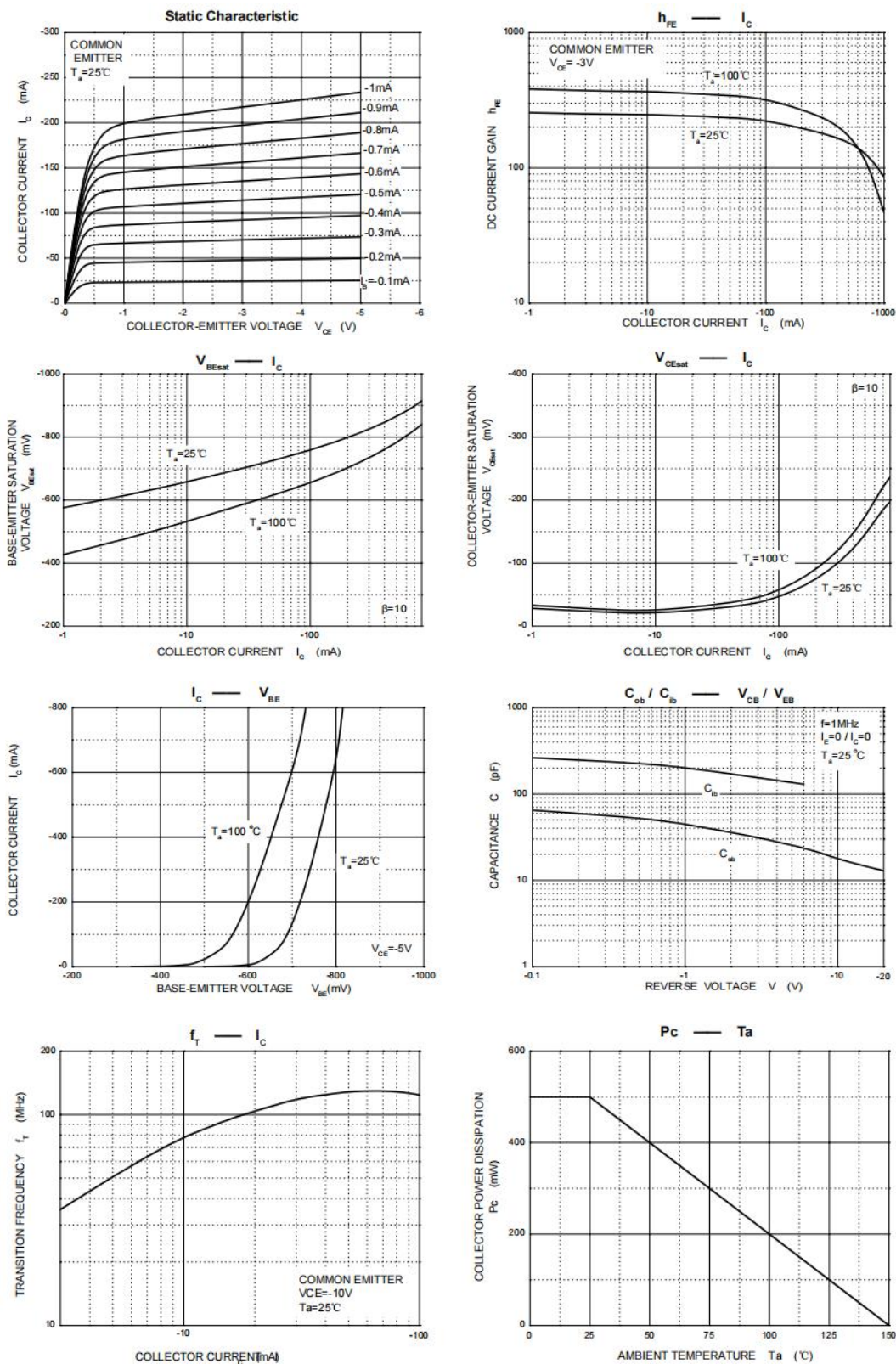


■Electrical Characteristics 电特性

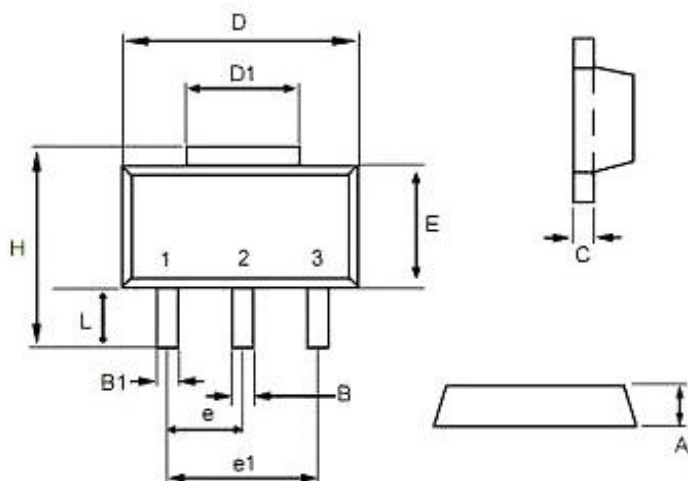
(TA=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I _C = -50μA, I _E =0)	BV _{CBO}	-80	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I _C = -2mA, I _B =0)	BV _{CEO}	-80	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I _E = -50μA, I _C =0)	BV _{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V _{CB} = -60V, I _E =0)	I _{CBO}	—	—	-1	μA
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = -4V, I _C =0)	I _{EBO}	—	—	-1	μA
DC Current Gain 直流电流增益(V _{CE} = -3V, I _C = -100mA)	H _{FE}	82	—	390	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I _C = -500mA, I _B = -50mA)	V _{CE(sat)}	—	—	-0.4	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(I _C = -500mA, I _B = -50mA)	V _{BE(sat)}	—	—	-1.2	V
Base-Emitter On Voltage 基极发射极导通电压(V _{CE} = -10V, I _C = -500mA)	V _{BE(on)}	—	—	-1.2	V
Transition Frequency 特征频率(V _{CE} = -5V, I _C = -50mA)	f _T	—	100	—	MHz
Output Capacitance 输出电容(V _{CB} = -10V, I _E =0, f=1MHz)	C _{ob}	—	25	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Dim	min	max
A	1.40	1.60
B	0.40	0.56
B1	0.35	0.48
C	0.35	0.44
D	4.40	4.60
D1	1.35	1.83
e	1.50 BSC	
e1	3.00 BSC	
E	2.29	2.60
H	3.75	4.25
L	0.80	1.20